

BCX79



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BCX79	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	DACTEDICTICS				
	RACTERISTICS	1		T	T
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	45		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \mu\text{A}, I_C = 0$	5.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, V_{BE} = 0.2 \text{ V},$ $T_A = +100 ^{\circ}\text{C}$		20	μΑ
I _{CES}	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, I_{E} = 0,$		10	nA
1	Emitter Cutoff Current	$V_{CE} = 45 \text{ V}, I_E = 0, T_A = +125 \text{ °C}$ $V_{EB} = 4.0 \text{ V}, I_C = 0$		2.5	μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$ $V_{CF} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	120 80	630 1,000	
		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	40	,	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$		0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$		1.0	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	0.6	0.7	V
		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$		0.9	V
SMALL S	IGNAL CHARACTERISTICS Collector-Base Capacitance	V _{CB} = 10 V, f = 1.0 MHz		4.5	pF
C _{eb}	Emitter-Base Capacitance	V _{EB} = 0.5 V, f = 1.0 MHz		15	pF
h _{ie}	Input Impedance	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz	1.6	8.5	kΩ
···le		1 1 - 1.0 N 12			
	Output Admittance	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz		100	μmhos
h _{oe}	Output Admittance Noise Figure	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$		100 6.0	μmhos dB
h _{oe} NF SWITCHI	Noise Figure NG CHARACTERISTICS	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ \ f = 1.0 \text{ kHz} \end{split}$		6.0	
NF SWITCHI	Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA} \end{split}$		6.0	dB
NF SWITCHI	Noise Figure NG CHARACTERISTICS Turn-on Time Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA} \\ V_{CC} &= 10 \text{ V}, \ I_C = 100 \text{ mA}, \\ V_{BB} &= 5.0 \text{ V}, \ I_{B1} = I_{B2} = 10 \text{ mA} \end{split}$		6.0 150 150	dB
NF SWITCHI	Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} I_C &= 2.0 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \ I_C = 0.2 \text{ mA}, \\ R_S &= 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz} \\ \end{split}$ $V_{CC} &= 10 \text{ V}, \ I_C = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \ I_{B1} = I_{B2} = 1.0 \text{ mA}, \\ V_{CC} &= 10 \text{ V}, \ I_C = 100 \text{ mA}, \\ \end{split}$		6.0	dB

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